TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

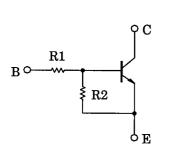
### RN1421,RN1422,RN1423,RN1424 RN1425,RN1426,RN1427

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

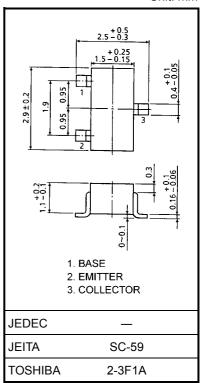
Unit: mm

- High current type (I<sub>C</sub> (max) = 800mA)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Low VCE (sat)
- Complementary to RN2401~RN2406

#### **Equivalent Circuit and Bias Resister Values**



Type No.	R1 (kΩ)	R2 (kΩ)
RN1421	1	1
RN1422	2.2	2.2
RN1423	4.7	4.7
RN1424	10	10
RN1425	0.47	10
RN1426	1	10
RN1427	2.2	10



Weight: 0.012 g (typ.)

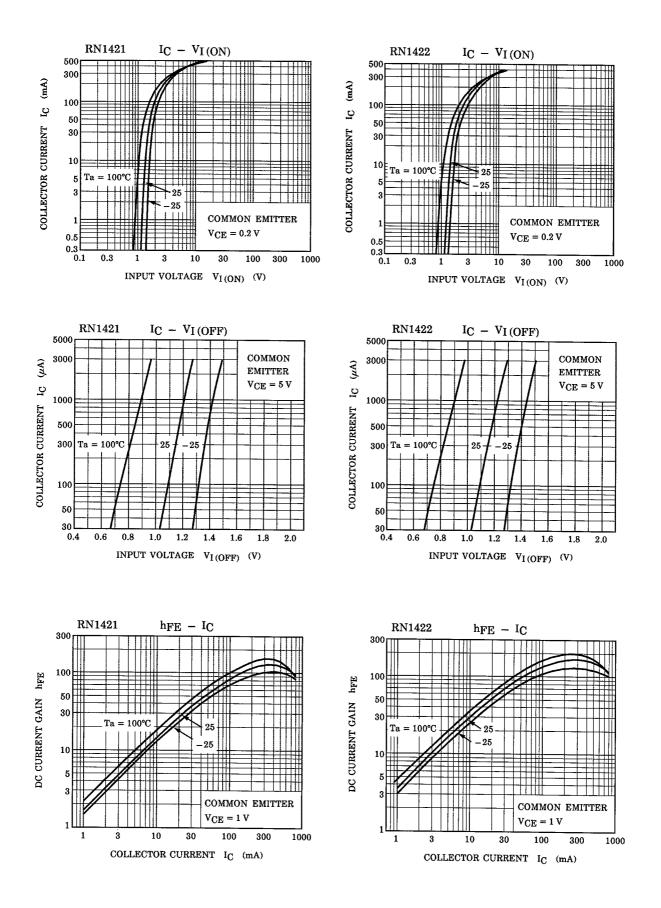
#### Maximum Ratings (Ta = 25°C)

Characterist	Symbol	Rating	Unit		
Collector-base voltage	RN1421~1427	V <sub>CBO</sub>	50	V	
Collector-emitter voltage	KIN1421*1427	V <sub>CEO</sub>	50	V	
	RN1421~1424		10	V	
Emitter-base voltage	RN1425, 1426	V <sub>EBO</sub>	5		
	RN1427		6		
Collector current		Ι <sub>C</sub>	800	mA	
Collector power dissipation	RN1421~1427	P <sub>C</sub>	200	mW	
Junction temperature	KIN 142 1* 1427	Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

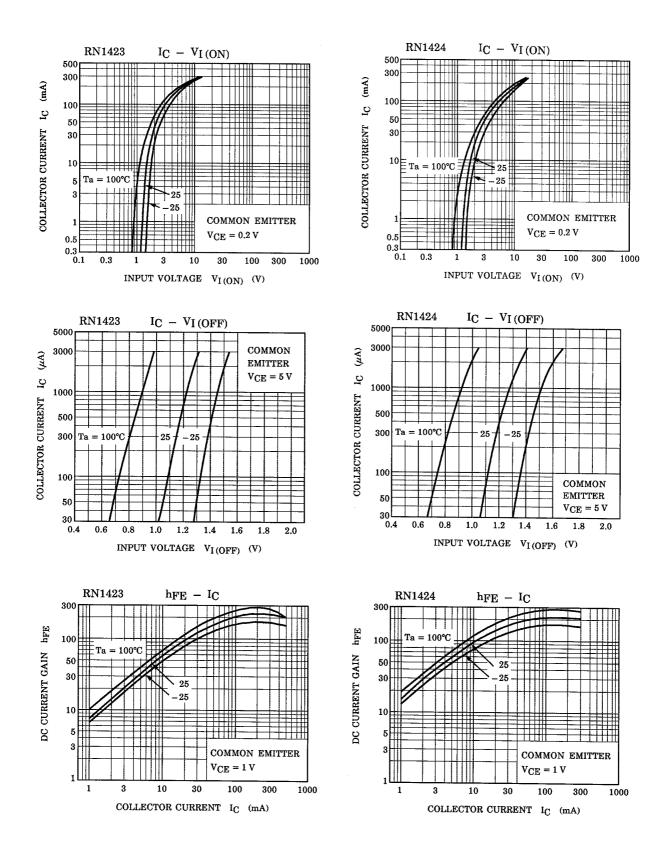
### Electrical Characteristics (Ta = 25°C)

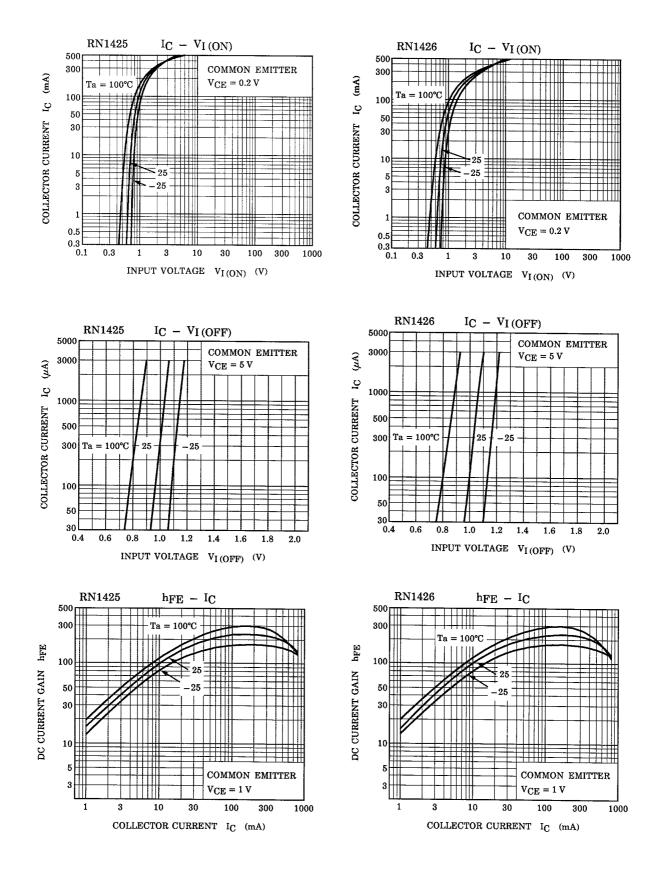
Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off	RN1421~1427	I <sub>CBO</sub>		V <sub>CB</sub> = 50V, I <sub>E</sub> = 0	_	_	100	۳Å
current	RIN 1421~1427	ICEO	—	V <sub>CE</sub> = 50V, I <sub>B</sub> = 0	_		500	nA
	RN1421				3.85		7.14	
	RN1422			(-10)(-10)	1.75	_	3.25	
	RN1423			$V_{EB} = 10V, I_C = 0$	0.82	_	1.52	
Emitter cut-off current	RN1424	I <sub>EBO</sub>	_		0.38		0.71	mA
	RN1425				0.365		0.682	
	RN1426			$V_{EB} = 5V, I_C = 0$	0.35		0.65	
	RN1427			V <sub>EB</sub> = 6V, I <sub>C</sub> = 0	0.378	-	0.703	
	RN1421				60	_	_	
	RN1422				65		_	
	RN1423				70	_	_	
DC current gain	RN1424	hee	_	V <sub>CE</sub> = 1V, I <sub>C</sub> = 100mA	90	_	_	
	RN1425	h <sub>FE</sub>			90	_	_	
	RN1426				90	_	_	
	RN1427				90	-	_	
Collector-emitter	RN1421~1427			I <sub>C</sub> = 50mA, I <sub>B</sub> = 2mA			0.25	V
saturation voltage	KIN 142 1* 1427	V <sub>CE (sat)</sub>		I <sub>C</sub> = 50mA, I <sub>B</sub> = 1mA			0.25	v
	RN1421	Vi (on)	_	V <sub>CE</sub> = 0.2V, I <sub>C</sub> = 100mA	1.0	_	3.5	V
	RN1422				1.4		4.5	
	RN1423				2.0		6.5	
Input voltage (ON)	RN1424				3.0		12.0	
	RN1425				0.6	_	2.0	
	RN1426				0.7	_	2.5	
	RN1427				1.0		3.0	
	RN1421~1424	V <sub>I (OFF)</sub>	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.1mA	0.8		1.3	
Input voltage (OFF)	RN1425, 1426				0.4		0.8	
	RN1427				0.5		1.0	
Transition frequency	RN1421~1427	f <sub>T</sub>	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 20mA	-	300	—	MHz
Collector Output capacitance	RN1421~1427	C <sub>ob</sub>	_	$V_{CB} = 10V, I_E = 0,$ f = 1MH <sub>z</sub>	_	7	_	pF
	RN1421				0.7	1.0	1.3	
	RN1422				1.54	2.2	2.86	
	RN1423	R1 ·	_	_	3.29	4.7	6.11	kΩ
Input resistor	RN1424				7	10	13	
	RN1425				0.329	0.47	0.61	
	RN1426				0.7	1.0	1.3	
	RN1427				1.54	2.2	2.86	
	RN1421~1424	R1/R2		_	0.9	1.0	1.1	- <u> </u>
Resistor ratio	RN1425		_		0.0423	0.047	0.0517	
	RN1426	111/174			0.09	0.1	0.11	
	RN1427				0.2	0.22	0.24	

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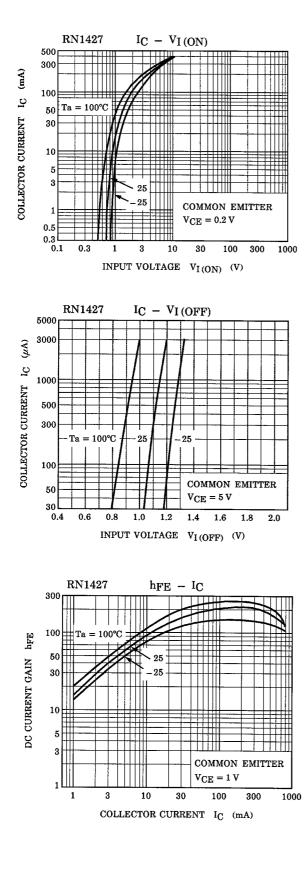


## TOSHIBA





# TOSHIBA



Type Name	Marking
RN1421	Q A
RN1422	Q B
RN1423	
RN1424	Q D U D
RN1425	Q E
RN1426	Q F
RN1427	Q G

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Handbook" etc.,

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